

<b>PCN Number:</b>	20240215001.1		<b>PCN Date:</b>	February 15, 2024																			
<b>Title:</b>	Qualification of RFAB using qualified Process Technology and Die Revision for select devices																						
<b>Customer Contact:</b>	Change Management team		<b>Dept:</b>	Quality Services																			
<b>Proposed 1<sup>st</sup> Ship Date:</b>	May 15, 2024		<b>Sample requests accepted until:</b>	March 16, 2024*																			
<b>*Sample requests received after March 16, 2024 will not be supported.</b>																							
<b>Change Type:</b>																							
<input type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Material																		
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Process																		
<input type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input checked="" type="checkbox"/>	Wafer Fab Site																		
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input checked="" type="checkbox"/>	Wafer Fab Material																		
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input checked="" type="checkbox"/>	Wafer Fab Process																		
<b>PCN Details</b>																							
<b>Description of Change:</b>																							
Texas Instruments is pleased to announce the addition of RFAB using the LBC9 qualified process technology in addition to a new die revision option for the devices listed below in the product affected section.																							
<table border="1"> <thead> <tr> <th colspan="3">Current Technology</th> <th colspan="3">New Technology</th> </tr> <tr> <th>Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>MIHO</td> <td>LBC8</td> <td>200 mm</td> <td>RFAB</td> <td>LBC9</td> <td>300 mm</td> </tr> </tbody> </table>						Current Technology			New Technology			Fab Site	Process	Wafer Diameter	Fab Site	Process	Wafer Diameter	MIHO	LBC8	200 mm	RFAB	LBC9	300 mm
Current Technology			New Technology																				
Fab Site	Process	Wafer Diameter	Fab Site	Process	Wafer Diameter																		
MIHO	LBC8	200 mm	RFAB	LBC9	300 mm																		
The die was also changed as a result of the process change.																							
Qual details are provided in the Qual Data Section.																							
<b>Reason for Change:</b>																							
Continuity of supply																							
<b>Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):</b>																							
None																							
<b>Changes to product identification resulting from this PCN:</b>																							
<b>Fab Site Information:</b>																							
Chip Site		Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City																			
MIHO8		MH8	JPN	Ibaraki																			
RFAB		RFB	USA	Richardson																			
<b>Die Rev:</b>																							
<b>Current</b>		<b>New</b>																					
Die Rev [2P]		Die Rev [2P]																					
B		C																					
Sample product shipping label (not actual product label)																							

TEXAS  
INSTRUMENTS  
MADE IN: Malaysia  
2DC: 2Q:



MSL 2 / 260C/1 YEAR SEAL DT  
MSL 1 / 235C/UNLIM 03/29/04

OPT:  
ITEM:  
LBL: 5A (L)T0:1750

(1P) SN74LS07NSR  
(Q) 2000 (D) 0336  
(31T) LOT: 3959047MLA  
(4W) TKY (1T) 7523483SI2  
(P)  
(2P) REV: (V) 0033317  
(20L) CSO: SHE (21L) CCO: USA  
(22L) ASO: MLA (23L) ACO: MYS

### Product Affected:

DRV5055A1QDBZR DRV5055A2QDBZR DRV5055A3QDBZR DRV5055A4QDBZR

### Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: DRV5055A1QDBZR	Qual Device: DRV5055A2QDBZR	Qual Device: DRV5055A3QDBZR	Qual Device: DRV5055A4QDBZR	QBS Reference: TLV62569DBVR	QBS Reference: TLV62569DBVR	QBS Reference: DRV5013A0ED8ZRQ1	QBS Reference: DRV5013A0QDBZRQ1	QBS Reference: TL4318QDBZRQ1	QBS Reference: PTMAG5253BA3QDBZR
HAST	A2	Biased HAST	130C	96 Hours	-	-	-	-	3/231/0	3/231/0	-	-	-	-
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0	-
UHAST	A3	Autoclave	121C/15psig	96 Hours	-	-	-	-	3/231/0	3/231/0	-	-	-	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	-	-	-	3/231/0	3/231/0	3/231/0	-
TC	A4	Temperature Cycle	-55C/150C	1000 Cycles	-	-	-	-	-	-	-	3/231/0	-	-
TC	A4	Temperature Cycle	-55C/150C	1500 Cycles	-	-	-	-	-	-	3/231/0	-	-	-
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	-	3/231/0	3/231/0	-	-	-	1/77/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	-	3/231/0	3/231/0	-	-	3/231/0	1/77/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	-	-	-	-	3/231/0	-	3/135/0	3/231/0	-
HTSL	A6	High Temperature Storage Life	150C	2000 Hours	-	-	-	-	-	-	3/135/0	-	-	-
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	-	-	-	3/231/0	-	-	-	-	-
HTOL	B1	Life Test	125C	1000 Hours	-	-	-	-	-	3/231/0	-	-	-	-
HTOL	B1	Life Test	150C	1000 Hours	-	-	-	-	-	-	1/77/0	-	-	-
HTOL	B1	Life Test	150C	300 Hours	-	-	-	-	3/231/0	-	-	1/77/0	-	-
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	-	-	-	3/3000/0	3/2400/0	-	-	-	-
SD	C3	PB Solderability	Precondition w/155C Dry Bake (4 hrs ±15 minutes)	-	-	-	-	-	-	-	1/15/0	1/15/0	-	-

Type	#	Test Name	Condition	Duration	Qual Device: DRV5055A1QDBZR	Qual Device: DRV5055A2QDBZR	Qual Device: DRV5055A3QDBZR	Qual Device: DRV5055A4QDBZR	QBS Reference: TLV62569DBVR	QBS Reference: TLV62569DBVR	QBS Reference: DRV5013A0ED8ZRQ1	QBS Reference: DRV5013A0QDBZRQ1	QBS Reference: TL4318QDBZRQ1	QBS Reference: PTMAG5253BA3QDBZR
SD	C3	PB-Free Solderability	Precondition w/155C Dry Bake (4 hrs ±15 minutes)	-	-	-	-	-	-	-	1/15/0	1/15/0	-	-
SD	C3	PB-Free Solderability	Precondition w/155C Dry Bake (4 hrs ±15 minutes); PB- Free Solder;	-	-	-	-	-	-	-	-	-	-	1/22/0
PD	C4	Physical Dimensions	CpIo1.67	-	-	-	-	-	-	-	3/30/0	3/30/0	3/30/0	-
ESD	E2	ESD CDM	-	1500 Volts	-	-	-	-	1/3/0	3/9/0	-	-	-	-
ESD	E2	ESD CDM	-	250 Volts	-	-	1/3/0	-	-	-	-	-	-	-
ESD	E2	ESD CDM	-	500 Volts	-	-	-	-	-	-	1/3/0	1/3/0	-	-
ESD	E2	ESD HBM	-	1000 Volts	-	-	1/3/0	-	-	-	-	-	-	-
ESD	E2	ESD HBM	-	2000 Volts	-	-	1/3/0	-	-	3/9/0	1/3/0	1/3/0	-	-
ESD	E2	ESD HBM	-	3500 Volts	-	-	-	-	1/3/0	3/9/0	-	-	-	-
LU	E4	Leach-Up	Per JE5078	-	-	-	1/3/0	-	1/6/0	3/9/0	1/6/0	1/6/0	-	-
CHAR	E5	Electrical Characterization	Min, Typ, Max Temp	-	-	-	1/30/0	-	1/30/0	3/90/0	-	-	-	-
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	-	-	1/30/0	-	1/30/0	3/90/0	-	-	-	-
CHAR	E5	Electrical Distributions	CpIo1.67 Room, hot and cold	-	-	-	-	-	-	-	2/60/0	3/90/0	3/90/0	-
FTY	E6	Final Test Yield	-	-	1/1/0	1/1/0	-	1/1/0	-	-	-	-	1/1/0	-

- QBS: Qual By Similarity
- Qual Device DRV5055A1QDBZR is qualified at MSL1 260C
- Qual Device DRV5055A2QDBZR is qualified at MSL1 260C
- Qual Device DRV5055A3QDBZR is qualified at MSL1 260C
- Qual Device DRV5055A4QDBZR is qualified at MSL1 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JE5047 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2303-072

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

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